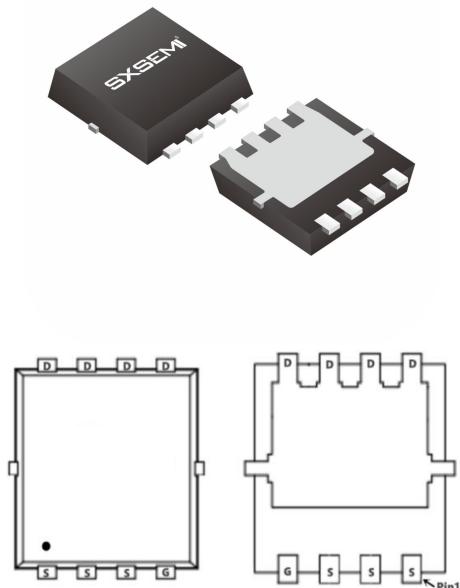


Description

The SX100P02NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

PDFN5*6-8L**General Features**

$V_{DS} = -20V$ $I_D = -100A$

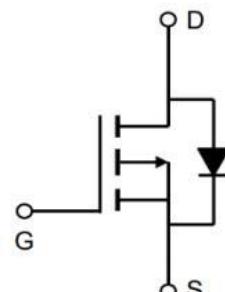
$R_{DS(ON)} < -2.7m\Omega$ @ $V_{GS} = -4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings (TC=25°C unless otherwise noted)**

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	± 12	V
I _D @T _c =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-100	A
I _D @T _c =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-66	A
I _{DM}	Pulsed Drain Current ²	-340	A
E _{AS}	Single Pulse Avalanche Energy ³	400	mJ
I _{AS}	Avalanche Current	-50	A
P _D @T _c =25°C	Total Power Dissipation ⁴	52.1	W
T _{TSG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C
R _{θJA}	Thermal Resistance Junction-Ambient ¹	25	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	1.8	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=-250\mu\text{A}$	-20	-	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=-20\text{V}, V_{GS}=0\text{V}$,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	$V_{DS}=0\text{V}, V_{GS}=\pm 12\text{V}$	-	-	± 100	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.4	0.6	-1.0	V
RDS(on)	Static Drain-Source on-Resistance	$V_{GS}=-4.5\text{V}, I_D=-30\text{A}$	-	2.1	2.7	$\text{m}\Omega$
RDS(on)	Static Drain-Source on-Resistance	$V_{GS}=-2.5\text{V}, I_D=-20\text{A}$	-	2.7	3.8	
RDS(on)	Static Drain-Source on-Resistance	$V_{GS}=-1.8\text{V}, I_D=-15\text{A}$	-	3.8	5.7	
Ciss	Input Capacitance	$V_{DS}=-10\text{V}, V_{GS}=0\text{V}, f=1.0\text{MHz}$	-	15	-	nF
Coss	Output Capacitance		-	1600	-	pF
Crss	Reverse Transfer Capacitance		-	1068	-	pF
Qg	Total Gate Charge	$V_{DS}=-10\text{V}, I_D=-20\text{A}, V_{GS}=-4.5\text{V}$	-	100	-	nC
Qgs	Gate-Source Charge		-	21	-	nC
Qgd	Gate-Drain("Miller") Charge		-	32	-	nC
td(on)	Turn-on Delay Time	$V_{DD}=-10\text{V}, R_L=0.5\Omega, V_{GS}=-4.5\text{V}, R_{GEN}=3\Omega$	-	20	-	ns
tr	Turn-on Rise Time		-	50	-	ns
td(off)	Turn-off Delay Time		-	100	-	ns
tf	Turn-off Fall Time		-	40	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-10	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-340	A
VSD	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=-30\text{A}$	-	-0.8	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $V_{DD}=-16\text{V}, V_{GS}=-4.5\text{V}, L=0.1\text{mH}, I_{AS}=-50\text{A}$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

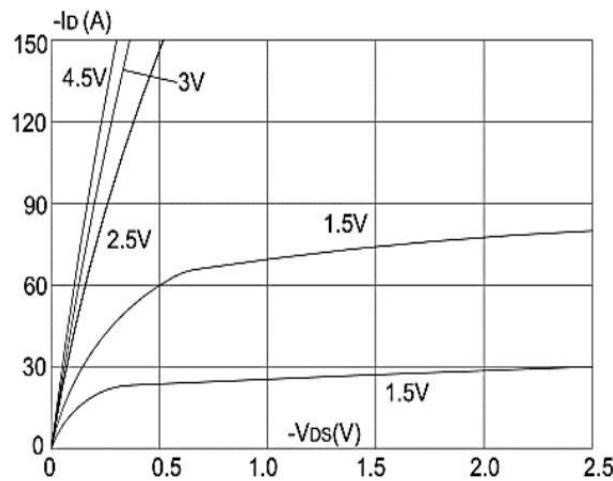


Figure 1: Output Characteristics

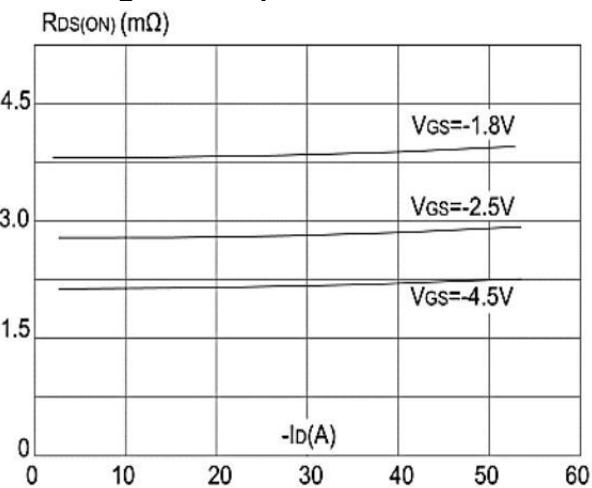


Figure 3: On-resistance vs. Drain Current

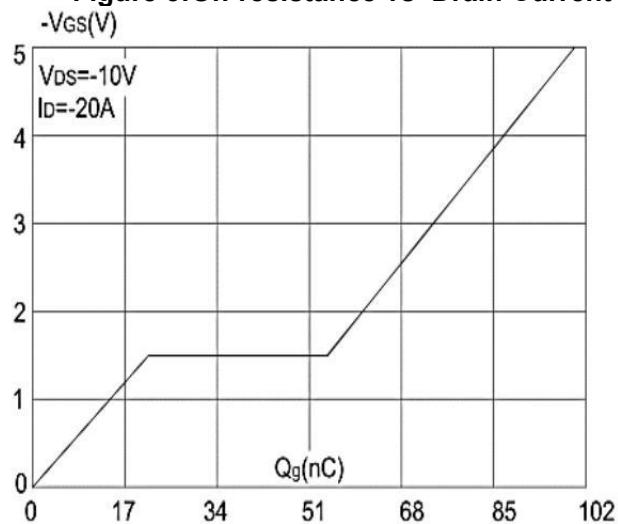


Figure 5: Gate Charge Characteristics

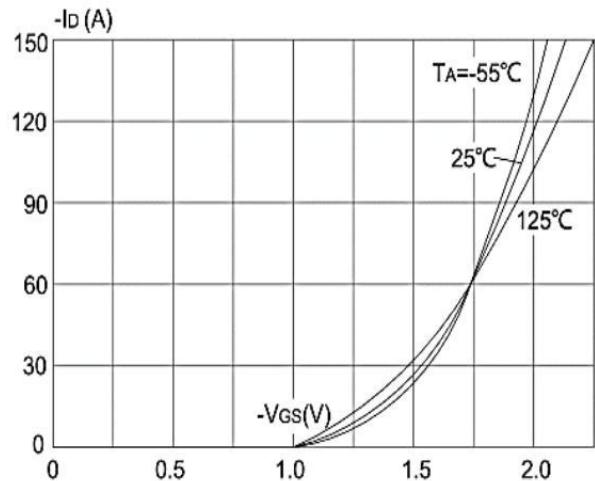


Figure 2: Typical Transfer Characteristics

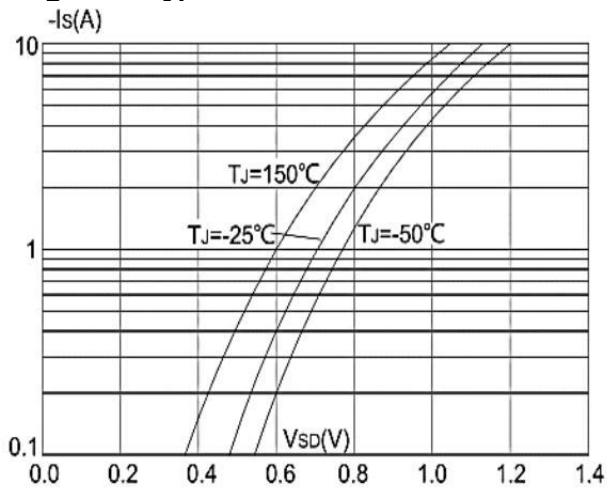


Figure 4: Body Diode Characteristics

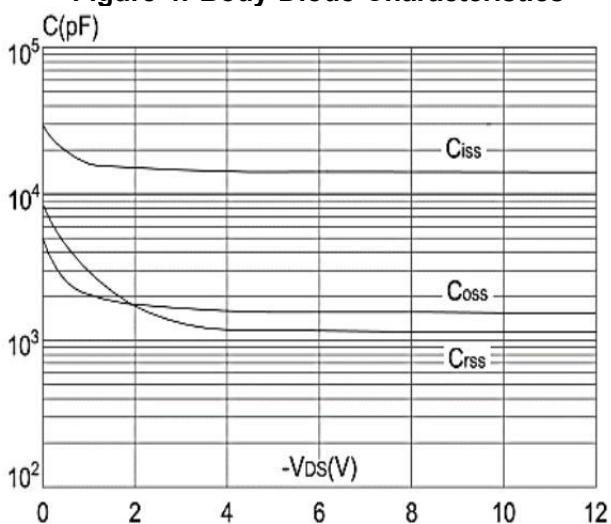


Figure 6: Capacitance Characteristics

Typical Characteristics

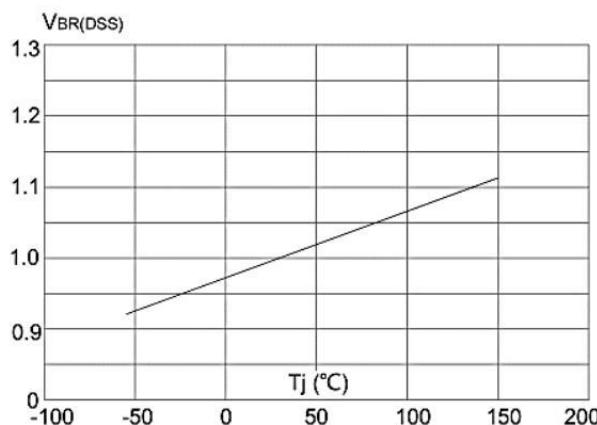


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

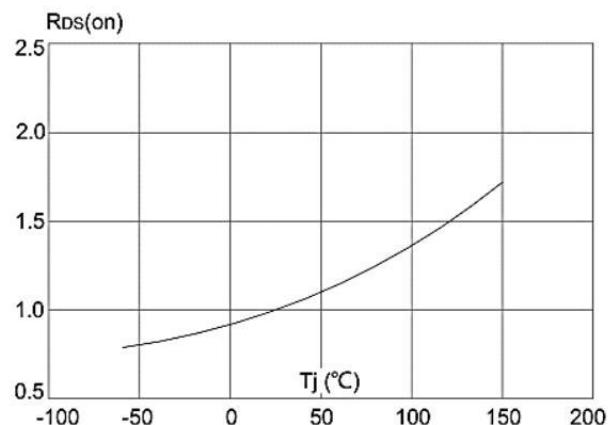


Figure 8: Normalized on Resistance vs. Junction Temperature

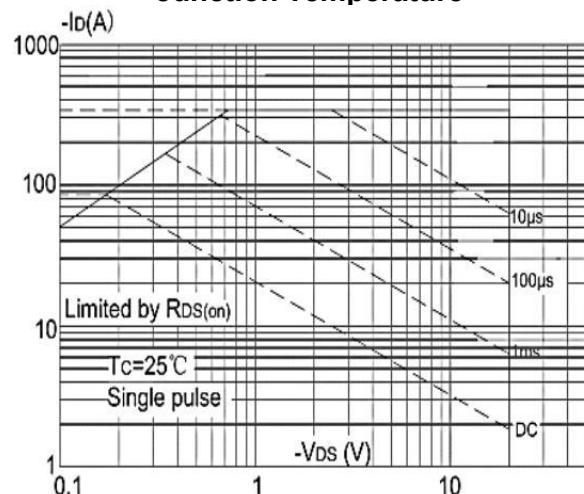


Figure 9: Maximum Safe Operating Area

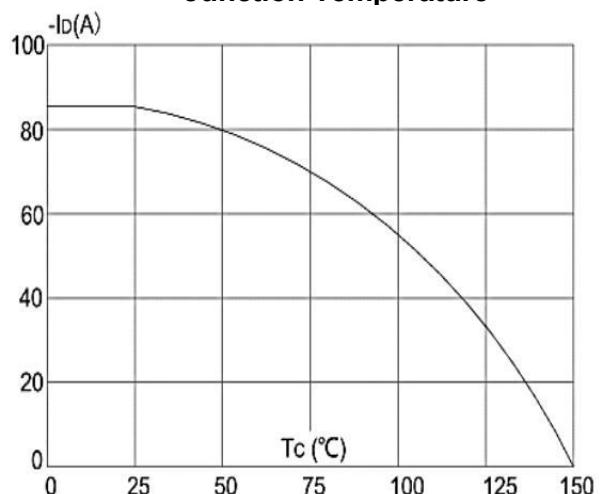


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

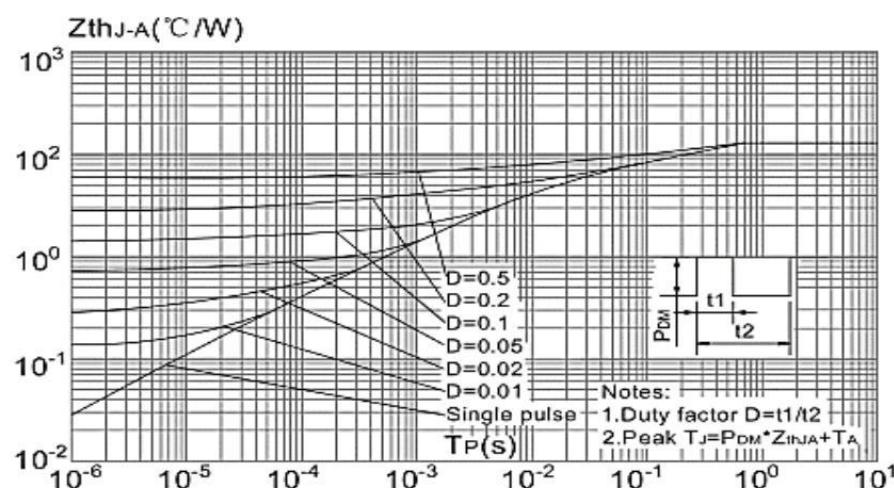
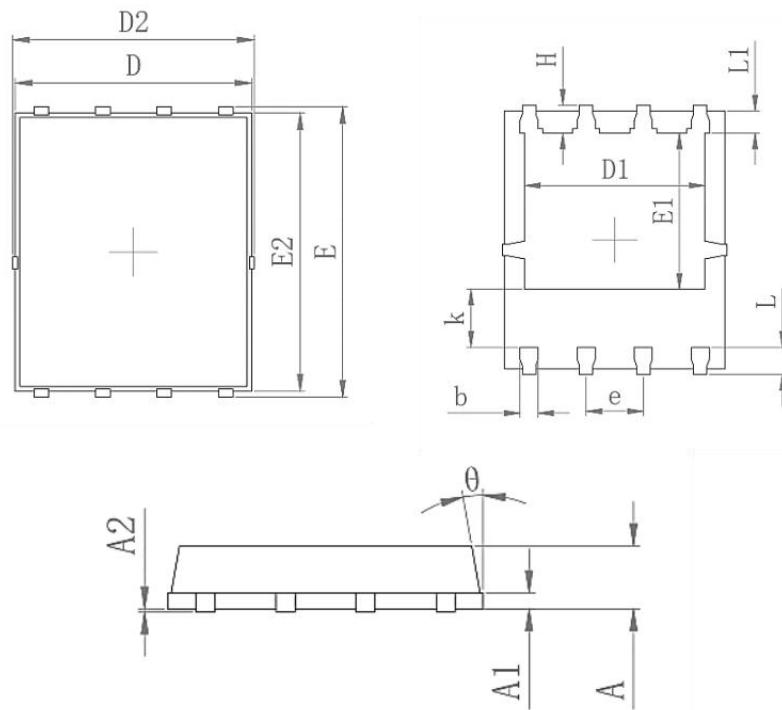


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

Package Mechanical Data-PDFN5X6-8L-XZT Single



Symbol	Common mm	
	Mim	Max
A	0.90	1.10
A1	0.254 REF	
A2	0-0.05	
D	4.824	4.976
D1	3.910	4.110
D2	4.944	5.076
E	5.924	6.076
E1	3.375	3.575
E2	5.674	5.826
b	0.350	0.450
e	1.270	
L	0.534	0.686
L1	0.424	0.576
K	1.190	1.390
H	0.549	0.701
Φ	8°	12°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000